Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1-27. (canceled)

28. (new) A method for controlling a non-volatile semiconductor memory system, the method comprising:

defining a plurality of physical blocks in a cell array of non-volatile semiconductor memory cells, each of the physical blocks including a plurality of non-volatile memory cells adapted for storing data;

storing address mapping information between the physical blocks and corresponding logical blocks in the physical blocks;

defining within the cell array at least first and second zones, each zone including at least one of the physical blocks;

preparing, in response to a power supply being turned on, a prepared address translation table comprising address translation information between logical blocks and physical blocks within the memory array, the prepared address translation table including address translation information for logical block addresses within at least the first zone and not including address translation information for logical block addresses within at least the second zone; and

determining that a requested logical block is not within the prepared address translation table and subsequently preparing a second address translation table comprising address translation information for logical block addresses within the second zone.

29. (new) A method for controlling a non-volatile semiconductor memory system, as set forth in claim 28, the method further comprising selectively replacing a defective physical block including defective cells with a redundant physical block so that, for each area, a quantity of defective physical blocks is less than or equal to a predetermined number.

30. (new) A method for controlling a non-volatile semiconductor memory system, the method comprising:

dividing a cell array of non-volatile semiconductor memory cells into a plurality of physical blocks;

storing in each of the physical blocks information corresponding to each relationship between the physical blocks and corresponding ones of logical blocks managed by the system;

storing in a random access memory in the system a first table for managing corresponding relationships between a first set of the logical blocks and the physical blocks of a first physical block zone including one or more of the physical blocks; and

determining in response to an access from a host that a requested logical block is not within the first table and subsequently storing in the random access memory a second table comprising relationships between a second set of the logical blocks and the physical blocks of a second physical block zone including one or more of the physical blocks.

31. (new) A method for controlling a non-volatile semiconductor memory system, as set forth in claim 30, the method further comprising selectively replacing a defective physical block including defective cells with a redundant physical block so that, for each area, a quantity of defective physical blocks is less than or equal to a predetermined number.